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distinguishing the portion 700 brought in contact with both the IC chip 1 and the board 4 from the other portion 701 as shown in Fig. 28C or to definitely distinguish them from each other as shown in Fig. 29C and Fig. 32A. That is, in Fig. 29C and Fig. 32A, it is acceptable to make the anisotropic conductive layer 10 have a multilayer structure further provided with a third resin layer 6z that located on the opposite side of the first resin layer 6x second resin respect to the layer 6у constructed of the insulating resin mixed with a smaller amount of inorganic filler than the first resin layer 6x or no inorganic filler 6f and bring the first resin layer 6x and the third resin layer 6z in contact with the IC chip 1 and the board 4, respectively.

Furthermore, as another modification example, it is acceptable to mix the portion 700 brought in contact with the IC chip 1 or the board 4 or both of them with the inorganic filler by less than 20 wt% or with no inorganic filler 6f and mix the other portion 701 with the inorganic filler by not less than 20 wt%. In this case, it is acceptable to gradually vary the amount of inorganic filler without definitely distinguishing the portion 700 brought in contact with the IC chip 1 or the board 4 or both of them from the other portion 701 as shown in Fig. 28A, 28B and 28C or to definitely distinguish them from each other

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as shown in Figs. 29A, 29B and 29C, Fig. 30, Fig. 31 and Fig. 32A. That is, it is possible to mix the first resin layer 6x or the first resin layer 6x and the third resin layer 6z with the inorganic filler by less than 20 wt% or with no inorganic filler 6f and mix the second resin layer 6y with the inorganic filler by not less than 20 wt%.

As concrete example, assuming that the insulating resin 6m is provided by thermosetting epoxy resin, then the second resin layer 6y occupies 50 wt% in the case of a ceramic board or 20 wt% in the case of a glass epoxy board. As an example, the first resin layer 6x or the third resin layer 6z or both of them are made to have a thickness of 15  $\mu\text{m}\text{,}$  while the second resin layer 6y is made to have a thickness of 40 to 60  $\mu m$ . The thickness of the anisotropic conductive layer 10 is made to have a dimension larger than the gap dimension obtained after the bonding of the IC chip 1 to the board 4, so that the space between the IC chip 1 and the board 4 is completely filled with the layer at the time of bonding of the IC chip 1 to the board 4, further ensuring the connection.

As another modification example, it is acceptable to reverse the loadings of the inorganic filler with respect to the modification example shown in Fig. 28C, Fig. 29C and Fig. 32A. That is, as shown in Fig. 28D, it is acceptable to make a middle portion 702 of the portion 703

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that belongs to the anisotropic conductive layer 10 and is brought in contact with both the IC chip 1 and the board 4is mixed with a smaller amount of inorganic filler than the portion 703 brought in contact with both the IC chip 1 and the board 4 or with no inorganic filler 6f. Also in this case, it is acceptable to gradually vary the amount of inorganic filler without definitely distinguishing the portion 703 brought in contact with both the IC chip 1 and the board 4 from the middle portion 702 or to definitely distinguish them from each other as shown in Fig. 29D and Fig. 32B. That is, as shown in Fig. 29D and Fig. 32B, the anisotropic conductive layer 10 can be provided with a fourth resin layer 6v constructed of the insulating resin 6m that is positioned in the portion brought in contact with the IC chip 1 and the board 4 and mixed with the inorganic filler 6f and a fifth resin layer 6w constructed of the insulating resin 6m that is positioned in the middle portion between the IC chip 1 and the board 4 and mixed with a smaller amount of inorganic filler than the fourth resin layer 6v or with no inorganic filler.

With this arrangement, the middle portion 702 located between the IC chip 1 and the board 4 or the fifth resin layer 6w is mixed with a smaller amount of inorganic filler than that of the portion 703 or the fourth resin layer 6v brought in contact with the IC chip 1 and the